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(57) **ABSTRACT**

A method for fabricating an integrated circuit device is disclosed. A substrate is provided and an integrated circuit area is formed on the substrate. The integrated circuit area includes a dielectric stack. A seal ring is formed in the dielectric stack and around a periphery of the integrated circuit area. A trench is formed around the seal ring and exposing a sidewall of the dielectric stack. The trench is formed within a scribe line. A moisture blocking layer is formed on the sidewall of the dielectric stack, thereby sealing a boundary between two adjacent dielectric films in the dielectric stack.

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